

isc Silicon PNP Power Transistor

2SA1002

DESCRIPTION

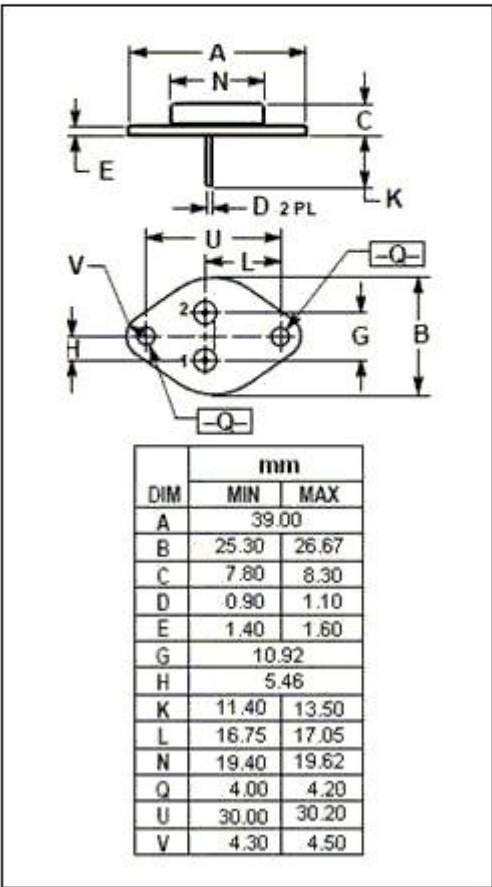
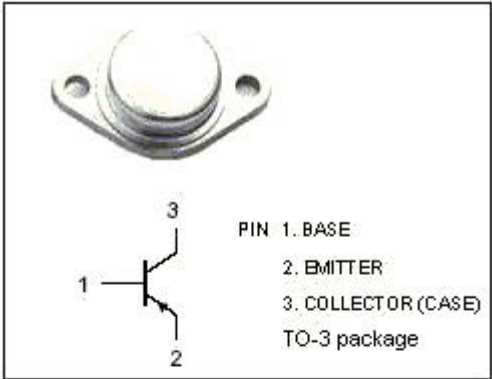
- High Current Capability
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min.})$

APPLICATIONS

- Designed for audio and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-120	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-12	A
P_C	Collector Power Dissipation @ $T_c=25^{\circ}C$	120	W
T_j	Junction Temperature	150	$^{\circ}C$
T_{stg}	Storage Temperature	-55~150	$^{\circ}C$



isc Silicon PNP Power Transistor**2SA1002****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30mA; I_B = 0$	-120			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -1mA; I_E = 0$	-120			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -1mA; I_C = 0$	-6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -8A; I_B = -0.8A$			-3.0	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120V; I_E = 0$			-50	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -6V; I_C = 0$			-50	μA
h_{FE}	DC Current Gain	$I_C = -0.5A; V_{CE} = -5V$	50		200	
f_T	Current-Gain—Bandwidth Product	$I_C = -1A; V_{CE} = -10V$	40			MHz